

ABSTRACT OF THE DISCLOSURE

A method for producing a semiconductor light emitting device is disclosed. The method comprises the step of growing a nitride type III-V group compound semiconductor layer that forms a light emitting device structure on a principal plane of a nitride type III-V group compound semiconductor substrate on which a plurality of second regions made of a crystal having a second average dislocation density are regularly arranged in a first region made of a crystal having a first average dislocation density so as to produce a semiconductor light emitting device, the second average dislocation density being greater than the first average dislocation density. The nitride type III-V group compound semiconductor layer does not directly contact the second regions on the principal plane of the nitride type III-V group compound semiconductor substrate.